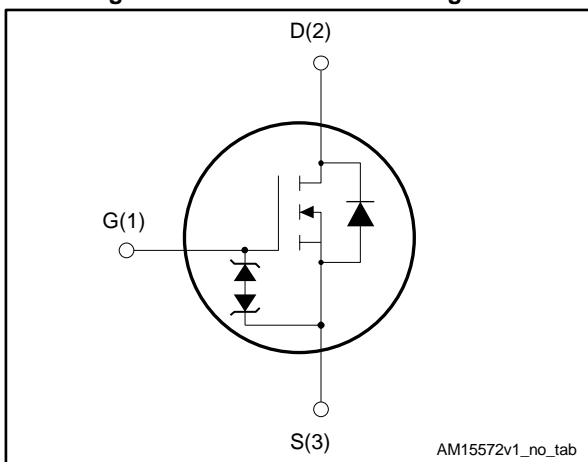


## N-channel 900 V, 0.21 $\Omega$ typ., 20 A MDmesh™ K5 Power MOSFET in a TO-247 package

Datasheet - production data



Figure 1: Internal schematic diagram



### Features

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>
STW20N90K5	900 V	0.25 $\Omega$	20 A

- Industry's lowest R<sub>DS(on)</sub> x area
- Industry's best FoM (figure of merit)
- Ultra-low gate charge
- 100% avalanche tested
- Zener-protected

### Applications

- Switching applications

### Description

This very high voltage N-channel Power MOSFET is designed using MDmesh™ K5 technology based on an innovative proprietary vertical structure. The result is a dramatic reduction in on-resistance and ultra-low gate charge for applications requiring superior power density and high efficiency.

Table 1: Device summary

Order code	Marking	Package	Packing
STW20N90K5	20N90K5	TO-247	Tube

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# 1 Electrical ratings

**Table 2: Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate-source voltage	$\pm 30$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	20	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	13	A
$I_D^{(1)}$	Drain current (pulsed)	80	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	250	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	4.5	V/ns
$dv/dt^{(3)}$	MOSFET $dv/dt$ ruggedness	50	
$T_j$	Operating junction temperature range	-55 to 150	$^\circ\text{C}$
$T_{stg}$	Storage temperature range		

**Notes:**

(1) Pulse width limited by safe operating area

(2)  $I_{SD} \leq 20\text{ A}$ ,  $di/dt \leq 100\text{ A}/\mu\text{s}$ ;  $V_{DS\text{ peak}} \leq V_{(BR)DSS}$ ,  $V_{DD} = 450\text{ V}$

(3)  $V_{DS} \leq 720\text{ V}$

**Table 3: Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	0.5	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient	50	$^\circ\text{C}/\text{W}$

**Table 4: Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not repetitive (pulse width limited by $T_{jmax}$ )	6.5	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	500	mJ

## 2 Electrical characteristics

$T_C = 25\text{ }^\circ\text{C}$  unless otherwise specified

**Table 5: On/off-state**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$ , $I_D = 1\text{ mA}$	900			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$ , $V_{DS} = 900\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$ , $V_{DS} = 900\text{ V}$ $T_C = 125\text{ }^\circ\text{C}^{(1)}$			50	$\mu\text{A}$
$I_{GSS}$	Gate body leakage current	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 100\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 10\text{ A}$		0.21	0.25	$\Omega$

**Notes:**

<sup>(1)</sup>Defined by design, not subject to production test

**Table 6: Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0\text{ V}$	-	1500	-	pF
$C_{oss}$	Output capacitance		-	120	-	pF
$C_{riss}$	Reverse transfer capacitance		-	1	-	pF
$C_{o(er)}^{(1)}$	Equivalent capacitance energy related	$V_{GS} = 0\text{ V}$ , $V_{DS} = 0\text{ to }720\text{ V}$	-	78	-	pF
$C_{o(tr)}^{(2)}$	Equivalent capacitance time related		-	220	-	pF
$R_g$	Intrinsic gate resistance	$f = 1\text{ MHz}$ , $I_D = 0\text{ A}$	-	3.7	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 720\text{ V}$ , $I_D = 20\text{ A}$	-	40	-	nC
$Q_{gs}$	Gate-source charge	$V_{GS} = 10\text{ V}$	-	14	-	nC
$Q_{gd}$	Gate-drain charge	(see <a href="#">Figure 14: "Test circuit for gate charge behavior"</a> )	-	17	-	nC

**Notes:**

<sup>(1)</sup> $C_{o(er)}$  is a constant capacitance value that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

<sup>(2)</sup> $C_{o(tr)}$  is a constant capacitance value that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 450\text{ V}$ , $I_D = 10\text{ A}$ , $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 13</a> : "Test circuit for resistive load switching times" and <a href="#">Figure 18</a> : "Switching time waveform")	-	20.2	-	ns
$t_r$	Rise time		-	13.5	-	ns
$t_{d(off)}$	Turn-off delay time		-	64.7	-	ns
$t_f$	Fall time		-	16	-	ns

Table 8: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		20	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		80	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 20\text{ A}$ , $V_{GS} = 0\text{ V}$	-		1.5	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 20\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ (see <a href="#">Figure 15</a> : "Test circuit for inductive load switching and diode recovery times")	-	517		ns
$Q_{rr}$	Reverse recovery charge		-	11.4		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	44		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 20\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$ (see <a href="#">Figure 15</a> : "Test circuit for inductive load switching and diode recovery times")	-	674		ns
$Q_{rr}$	Reverse recovery charge		-	14		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	41.6		A

**Notes:**

(1)Pulse width limited by safe operating area

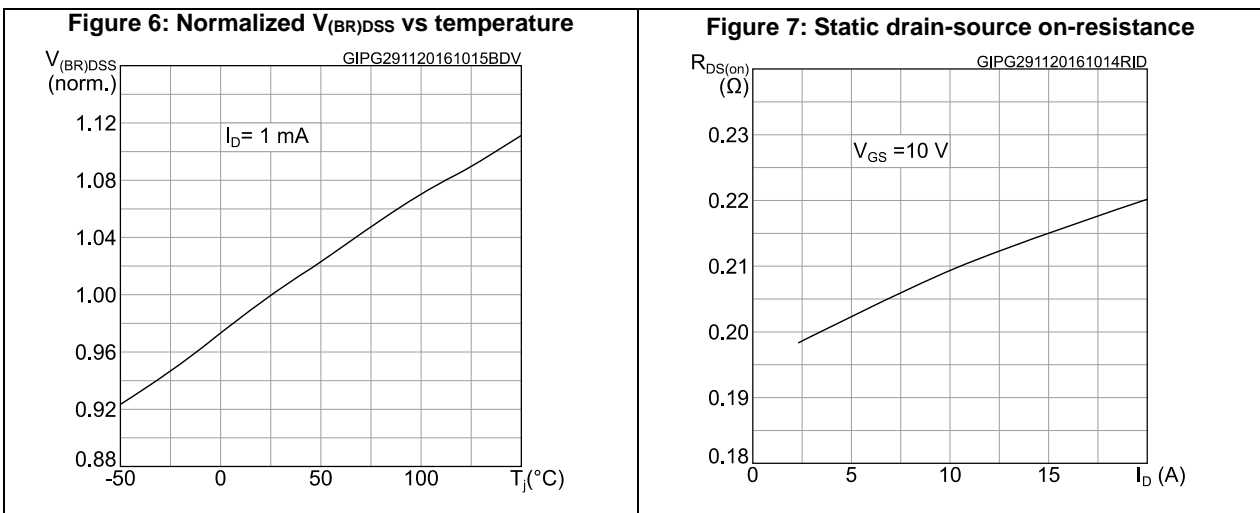
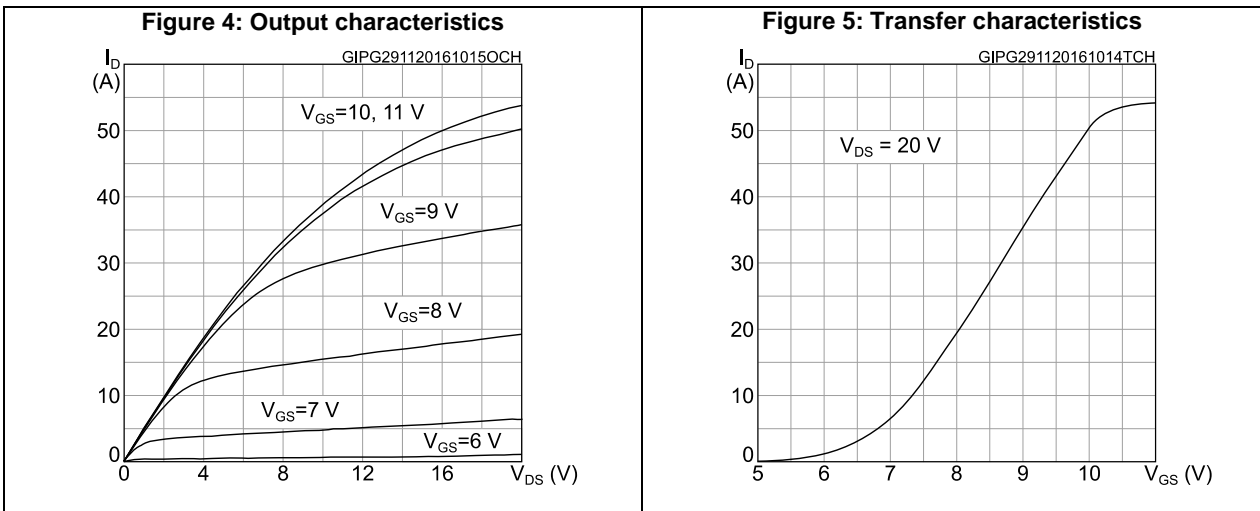
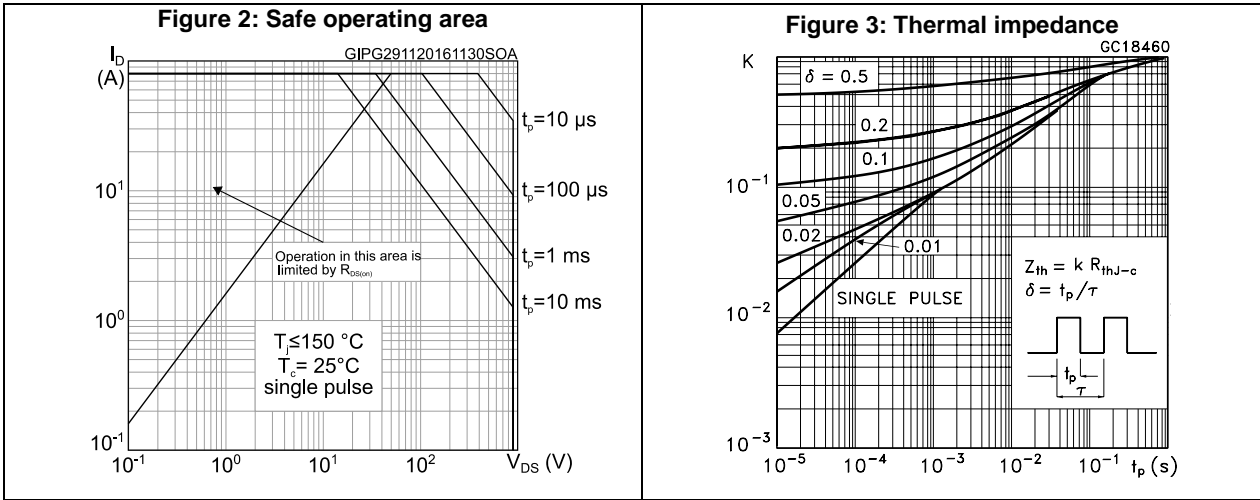
(2)Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

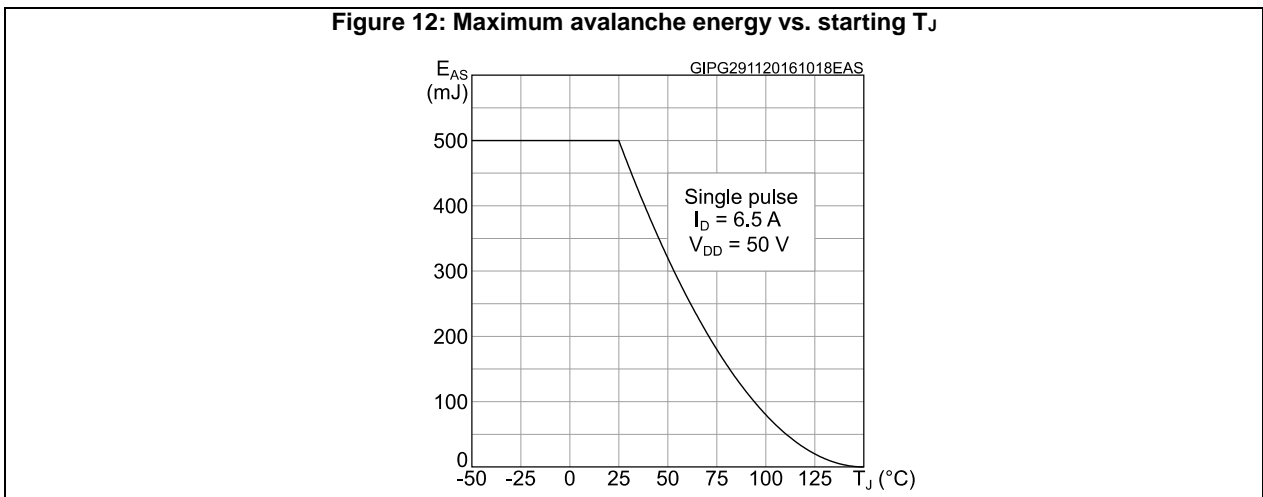
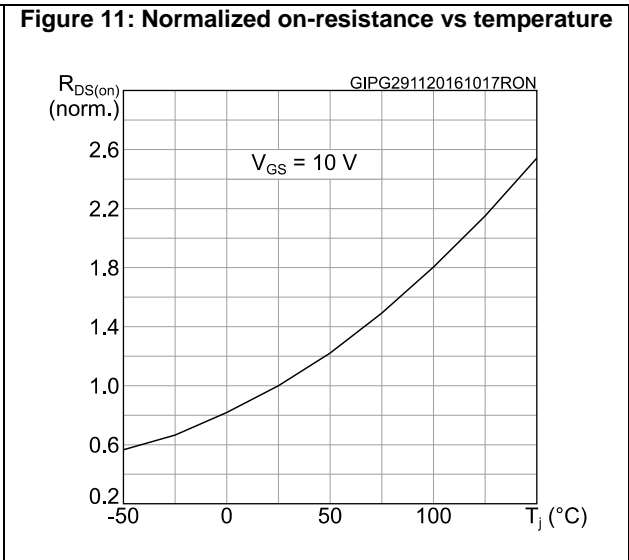
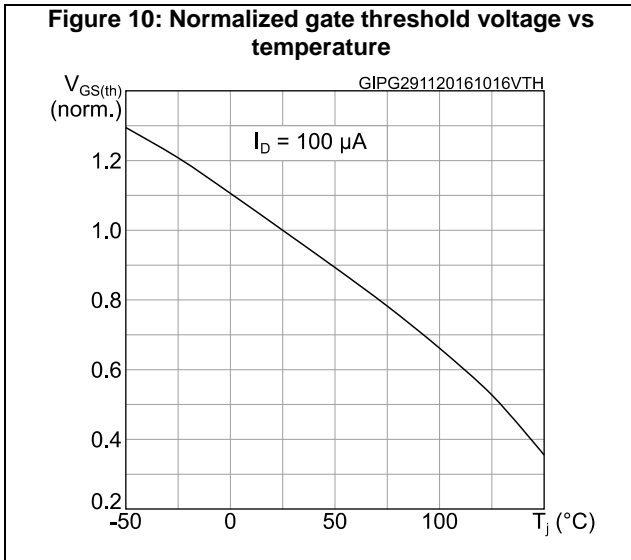
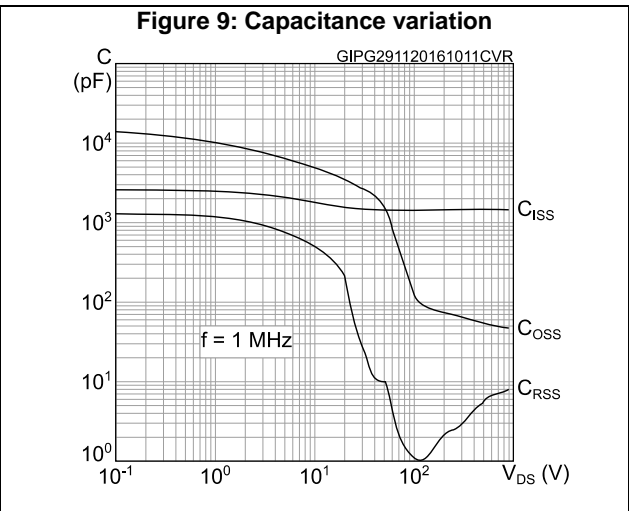
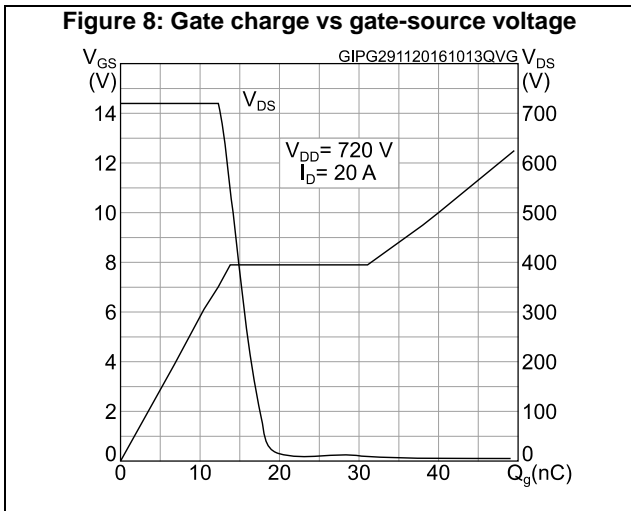
Table 9: Gate-source Zener diode

Symbol	Parameter	Test conditions	Min	Typ	Max.	Unit
$V_{(BR) GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1\text{ mA}$ , $I_D = 0\text{ A}$	30	-	-	V

The built-in back-to-back Zener diodes are specifically designed to enhance the ESD performance of the device. The Zener voltage facilitates efficient and cost-effective device integrity protection, thus eliminating the need for additional external componentry.

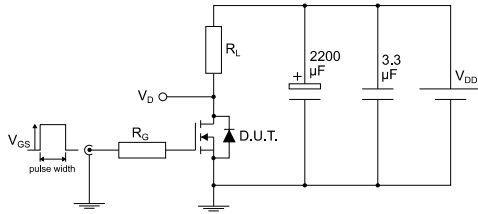
## 2.1 Electrical characteristics (curves)





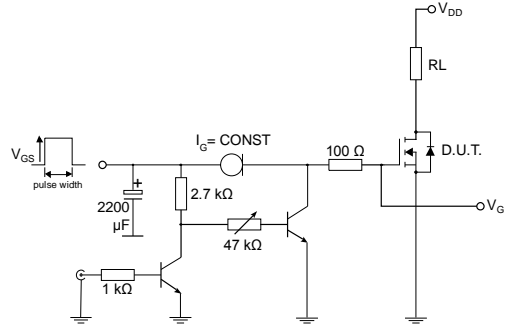
### 3 Test circuits

**Figure 13: Test circuit for resistive load switching times**



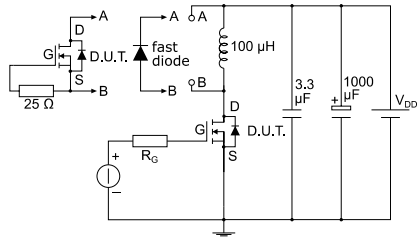
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**Figure 14: Test circuit for gate charge behavior**



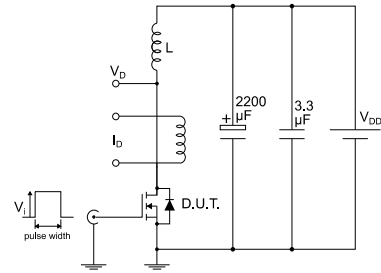
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**Figure 15: Test circuit for inductive load switching and diode recovery times**



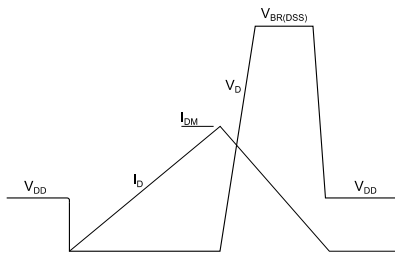
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**Figure 16: Unclamped inductive load test circuit**



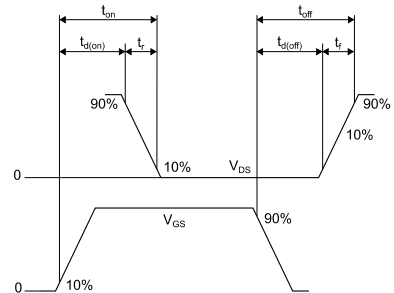
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**Figure 17: Unclamped inductive waveform**



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**Figure 18: Switching time waveform**



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## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

### 4.1 TO-247 package information

Figure 19: TO-247 package outline

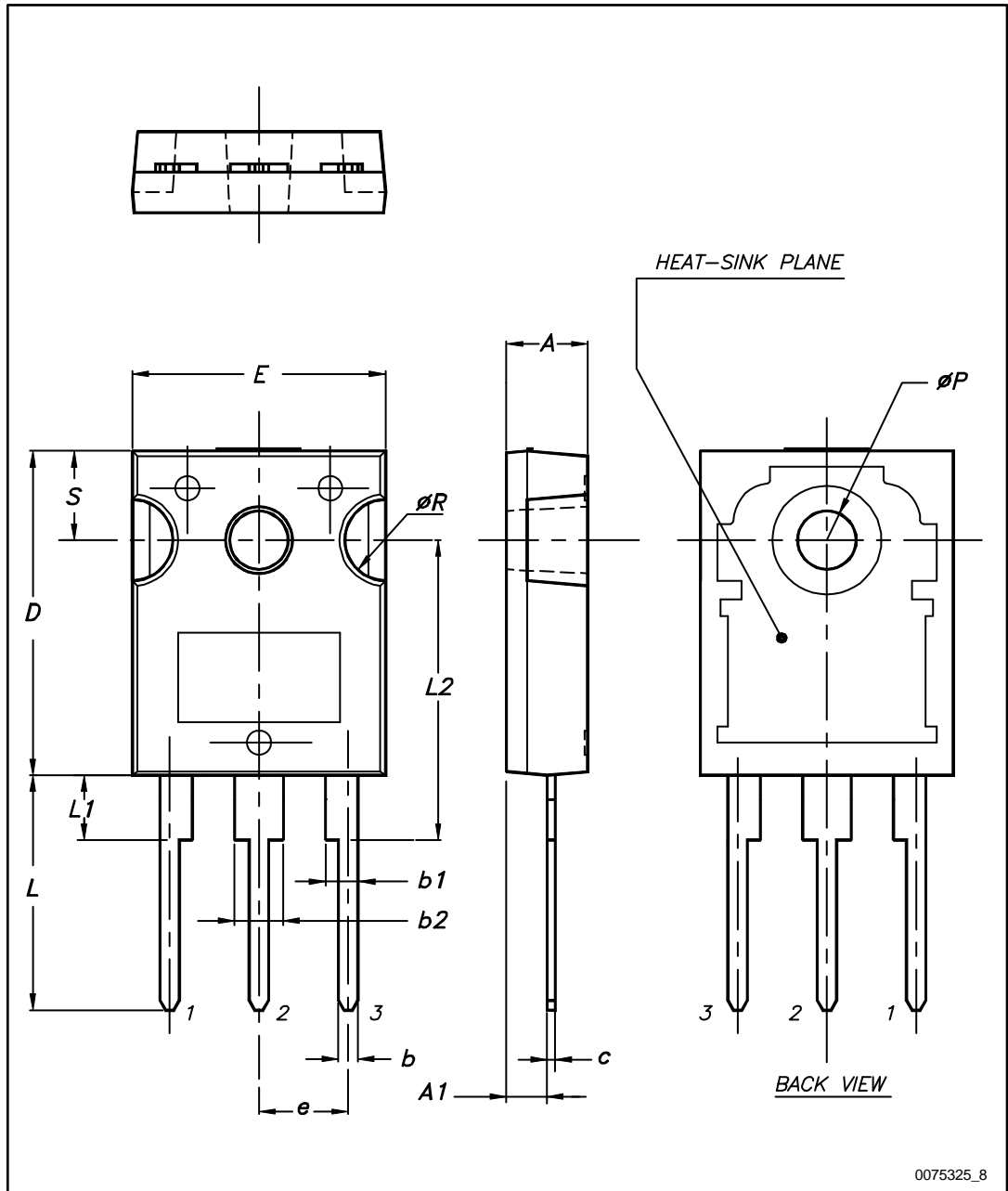


Table 10: TO-247 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

## 5 Revision history

**Table 11: Document revision history**

Date	Revision	Changes
19-May-2016	1	First release.
01-Dec-2016	2	Modified: title and $R_{DS(on)}$ value in cover page Modified: <a href="#">Table 4: "Avalanche characteristics"</a> <a href="#">Table 5: "On/off-state"</a> , <a href="#">Table 6: "Dynamic"</a> , <a href="#">Table 7: "Switching times"</a> and <a href="#">Table 8: "Source-drain diode"</a> Added <a href="#">Section 2.1: "Electrical characteristics (curves)"</a> Modified: <a href="#">Section 3: "Test circuits"</a> Datasheet promoted from preliminary data to production data Minor text changes

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